
2SB1530

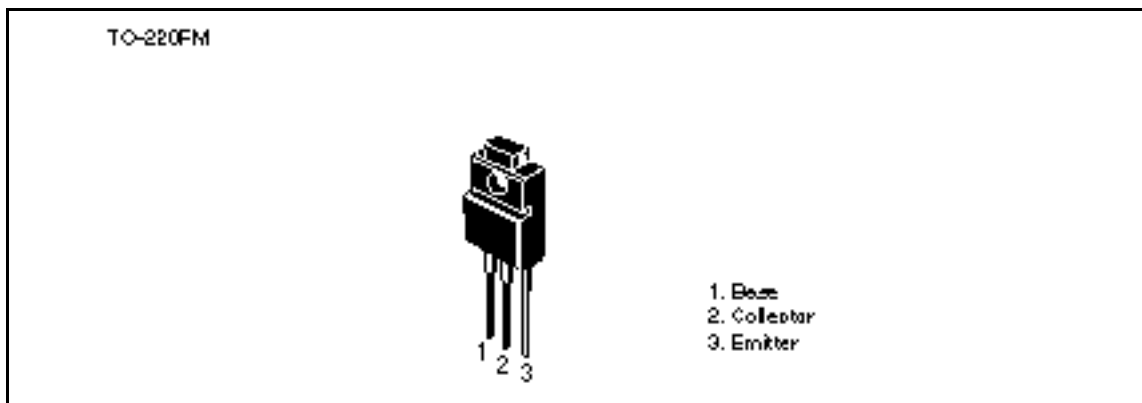
Silicon PNP Triple Diffused

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Application

Low frequency power amplifier color TV vertical deflection output complementary pair with 2SD2337

Outline



2SB1530

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-200	V
Collector to emitter voltage	V_{CEO}	-150	V
Emitter to base voltage	V_{EBO}	-6	V
Collector current	I_C	-2	A
Collector peak current	$I_{C(peak)}$	-5	A
Collector power dissipation	P_C	1.5	W
	P_C^{*1}	20	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-45 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$.

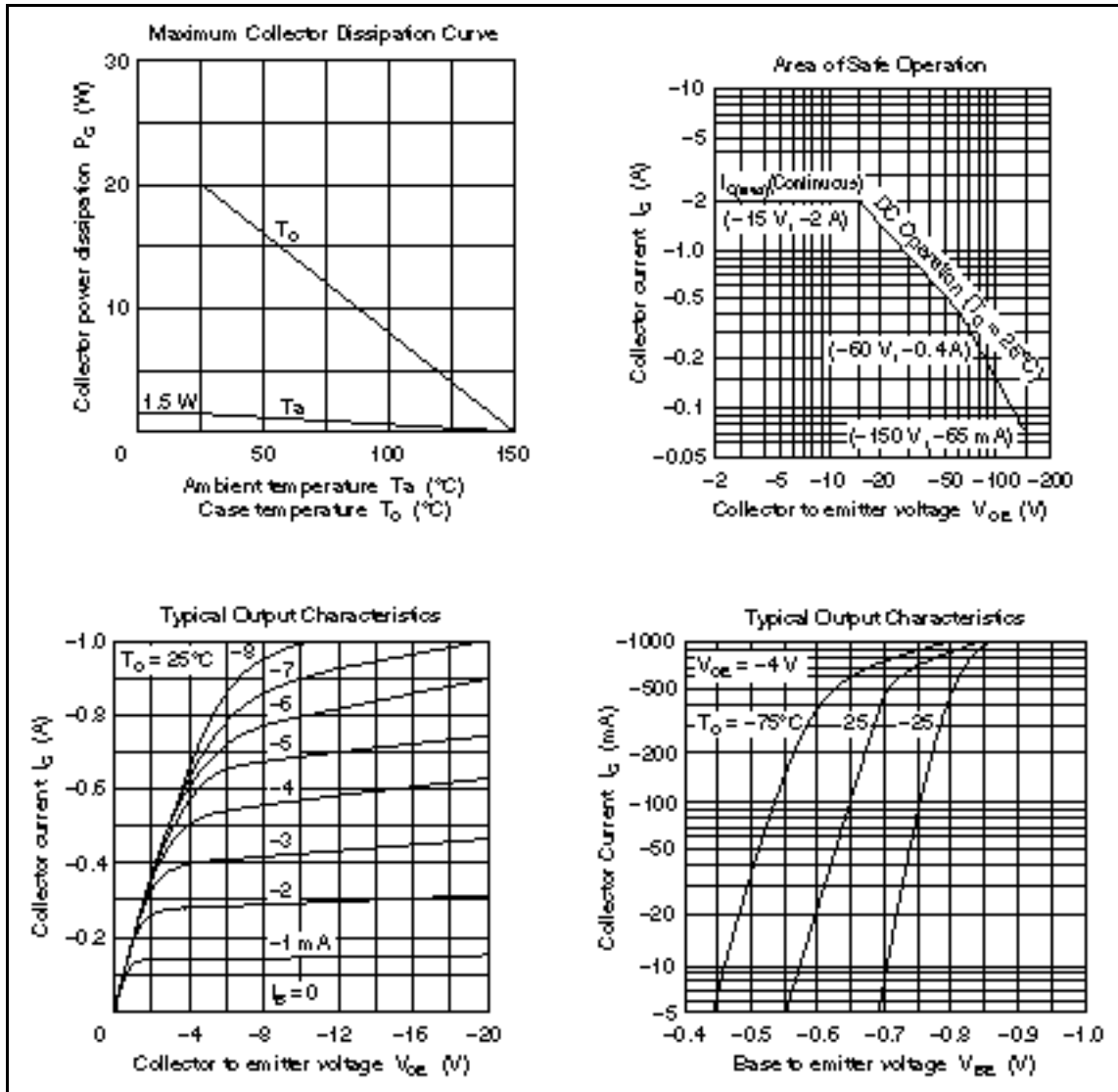
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-150	—	—	V	$I_C = -50\text{ mA}$, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	—	—	V	$I_E = -5\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1	μA	$V_{CB} = -120\text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200		$V_{CE} = -4\text{ V}$, $I_C = -50\text{ mA}$
	h_{FE2}	60	—	—		$V_{CE} = -10\text{ V}$, $I_C = -500\text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-3	V	$I_C = -500\text{ mA}$, $I_B = -50\text{ mA}$
Base to emitter voltage	V_{BE}	—	—	-1	V	$I_{CE} = -4\text{ A}$, $I_C = -50\text{ mA}$

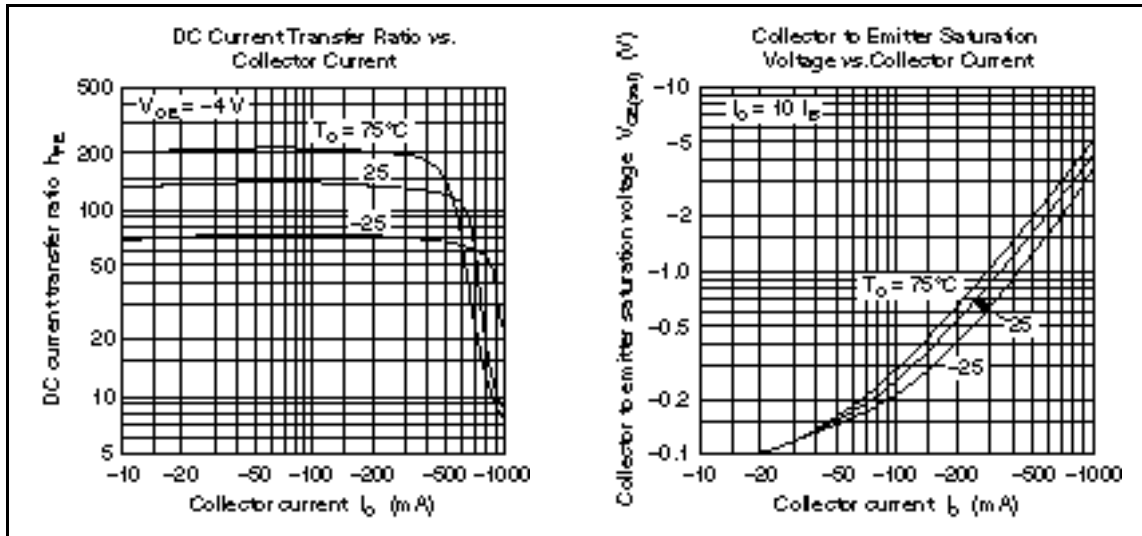
Notes: 1. The 2SB1530 is grouped by h_{FE1} as follows.

B	C
60 to 120	100 to 200

2. Pulse test.



2SB1530



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